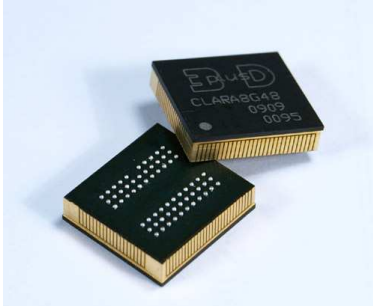


DDR2 Synchronous Dynamic Ram MODULE

3D2D8G08UB2322

8Gbit DDR2 SDRam organized as 1Gx8, based on 256Mx8



Target application

- Embedded Systems
- Workstations
- Server
- Super computers
- Test systems

Pin Assignment

FBGA 65 (Pitch 0.80mm)

Top View
(Viewed by Transparency)

Pin Indicator



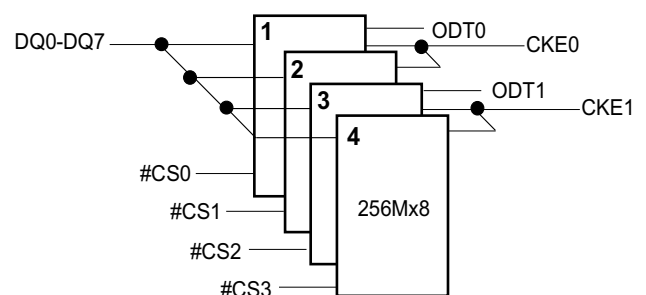
Features and Benefits

- JEDEC-standard 65 balls
- **Highest Memory Density**
- Vdd=VddQ = +1.8V +/-0.1V
- 4n-bit prefetch architecture
- DLL to align DQ and DQS transition with CK
- 8 internal banks per memory
- Programmable CAS latency
- Posted CAS additive latency
- Write Latency(WL) = Read Latency(RL) -1 t_{ck}
- Programmable burst lengths: 4 or 8
- Adjustable data-output drive strength
- Differential data-strobe
- 64ms, 8,192-cycle refresh
- On-Die Termination (ODT)
- Data rate available : 400Mbps (CL3), 533Mbps (CL4) and 667Mbps (CL5)
- Commercial, Industrial and Military temperature range.

General description

3D Plus offers a new **8Gbit DDR2 SDRAM** cube with a **compatible JEDEC standard package**. This is the highest memory density. It enables **50% board area savings** against any other solution. This cube embeds 4 chips with a capacity of 2Gb (256Mbx8) each. They can be addressed with separates CS, CKE and ODT. Our products are available at 200, 267 and 333 clock speed which is equivalent to 400, 533 and 667 Mbps in Commercial, Industrial and Military temperature range. Thanks to the **high density patented technology** and the **cold manufacturing process** the memories are embedded in a small form factor cube without compromising electrical or thermal performance. This device is ideal for high density memory applications that require high speed transfer and compatibility with standards servers and networking equipment.

FUNCTIONAL BLOCK DIAGRAM



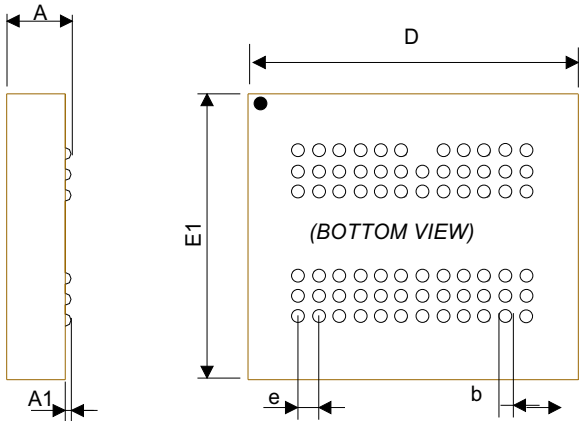
(All other signals are common to the two memories)

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Mechanical Drawing



	Min	Max
A	2.90	3.10
A1	0.17	0.20
D	14.50	14.70
E1	12.50	12.70
b	0.40	
e	0.80	
Dimensions (mm)		
Max. weight : 1.00 gr.		

DC Operating conditions and characteristics

Parameter	Symbol	Min	Max	Unit
Supply Voltage relative to Vss	V _{DD}	1.7	1.9	V
Supply voltage relative to VssQ	V _{DDQ}	1.7	1.9	V
Supply voltage relative to VssL	V _{DDL}	1.7	1.9	V
I/O Reference Voltage	V _{REF}	0.49xV _{DDQ}	0.51xV _{DDQ}	V
I/O Termination Voltage (syst.)	V _{TT}	V _{REF} -0.04	V _{REF} +0.04	V
Input High (Logic1) Voltage	V _{IH} (DC)	V _{REF} +0.125	V _{DDQ} +0.3	V
Input Low (Logic0) Voltage	V _{IL} (DC)	-0.3	V _{REF} -0.125	V

Absolute maximum ratings

Parameter	Symbol	Value	Unit
Voltage on any ball relative to VSS	V _{IN} , V _{OUT}	-0.5 ~ +2.3	V
Storage temperature	T _{STG}	-55 ~ +150	°C

DC Characteristics

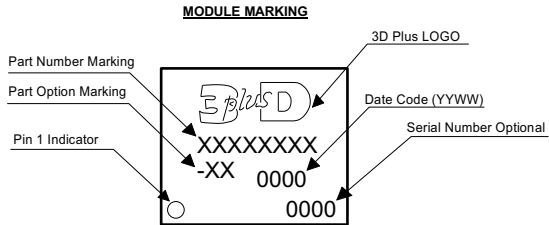
Parameter	Symbol	Value	Unit
Operating current (One bank active)	I _{DD1}	160	mA
Precharge power down current	I _{DD2P}	30	mA
Self refresh current	I _{DD6}	30	mA

3D2D8G08UB2322 - X

Temperature Range

C = (0°C to +70°C)
I = (-40°C to +85°C)
M = (-55°C to +125°C)

MODULE MARKING



Part Number Marking: XXXXXXXXXX-XX
 Date Code (YYWW): 0000
 Pin 1 Indicator: 0000

MAIN SALES OFFICE

	3D PLUS	Tel :	Fax :	Web :	DISTRIBUTOR
FRANCE	3D PLUS 408, rue Hélène Boucher Z.I. 78532 BUC Cedex	33 (0)1 30 83 26 50	33 (0)1 39 56 25 89	www.3d-plus.com e-mail : sales@3d-plus.com	
USA	3D PLUS USA, Inc 6633 Eldorado Parkway Suite 420 Mckinney, TX 75070	(214) 733-8505	(214) 733-8506	e-mail : sales@3d-plus.com	

DDR2 Memory Module

CLARA8G8